SOES019A - OCTOBER 1995 - REVISED JULY 1996



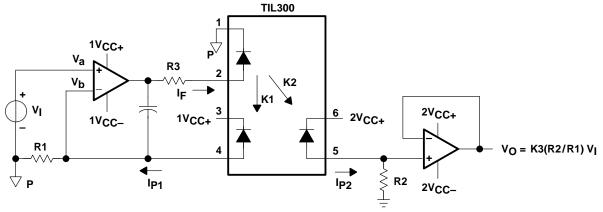
- Wide Bandwidth . . . > 200 kHz
- High Transfer-Gain Stability . . . ±0.05%/°C
- 3500 V Peak Isolation
- UL Approval Pending
- Applications
 - Power-Supply Feedback
 - Medical-Sensor Isolation
 - Opto Direct-Access Arrangement (DAA)
 - Isolated Process-Control Transducers

NC - No internal connection

description

The TIL300 precision linear optocoupler consists of an infrared LED irradiating an isolated feedback photodiode and an output photodiode in a bifurcated arrangement. The feedback photodiode captures a percentage of the flux of the LED and generates a control signal that can be used to regulate the LED drive current. This technique is used to compensate for the nonlinear time and temperature characteristics of the LED. The output-side photodiode produces an output signal that is linearly proportional to the servo-optical flux emitted from the LED.

A typical application circuit (shown in Figure 1) uses an operational amplifier as the input to drive the LED. The feedback photodiode sources current through R1, which is connected to the inverting input of the input operational amplifier. The photocurrent I_{P1} assumes a magnitude that satisfies the relationship $I_{P1} = V_I/R1$. The magnitude of the current is directly proportional to the LED current through the feedback transfer gain $K1(V_I/R1 = K1 \times I_F)$. The operational amplifier supplies LED current to produce sufficient photocurrent to keep the node voltage V_b equal to node voltage V_a .



NOTES: A. K1 is servo current gain, the ratio of the feedback photodiode current (IP1) to the input LED current (IF), i.e. K1 = IP1/IF.

- B. K2 is forward gain, the ratio of the output photodiode current (I_{P2}) to the input LED current (I_{F}), i.e. $K2 = I_{P2}/I_{F}$.
- C. K3 is transfer gain, the ratio of the forward gain to the servo gain, i.e. K3 = K2/K1.

Figure 1. Typical Application Circuit



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Terminal Functions

TERMINAL		1/0	DESCRIPTION				
NAME	NO.	1/0	DESCRIPTION				
LEDK	1		LED cathode				
LEDA	2		LED anode				
PDK1	3		odiode 1 cathode				
PDA1	4		otodiode 1 anode				
PDA2	5		todiode 2 anode				
PDK2	6		todiode 2 cathode				
NC	7		internal connection				
NC	8		No internal connection				

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

	it		

Continuous total power dissipation (see Note 1)	160 mW
Input LED forward current, I _F	60 mA
Surge current with pulse width < 10 μs	250 mA
Reverse voltage, V _R	5 V
Reverse current, I _R	10 μΑ

Detector

Continuous power dissipation	(see Note 2)	50 mW
Reverse voltage, V _R		50 V

Coupler

o upio	
Continuous total power dissipation (see Note 3)	210 mW
Storage temperature, T _{stq}	5°C to 150°C
Operating temperature, T _A –55	5°C to 100°C
Input-to-output voltage	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. Derate linearly from 25°C at a rate of 2.66 mW/°C.
 - 2. Derate linearly from 25°C at a rate of 0.66 mW/°C.
 - 3. Derate linearly from 25°C at a rate of 3.33 mW/°C.

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electrical characteristics at $T_A = 25$ °C

Emitter

PARAMETER		CON	CONDITIONS			MAX	UNIT
٧F	Forward voltage	I _F = 10 mA			1.25	1.50	V
	Temperature coefficient of V _F				-2.2		mV/°C
I_{R}	Reverse current	V _R = 5 V				10	μΑ
t _r	Rise time	$I_F = 10 \text{ mA},$	$\Delta I_F = 2 \text{ mA}$		1		μs
t _f	Fall time	I _F = 10 mA,	$\Delta I_F = 2 \text{ mA}$		1		μs
Ci	Junction capacitance	$V_{F} = 0,$	f = 1 MHz		15		pF

Detector

PARAMETER		CONDITIONS		MIN	TYP [†]	MAX	UNIT
I _{DK} †	Dark current	V _R = 15 V,	IF = 0			25	nA
	Open circuit voltage	I _F = 10 mA			0.5		V
los	Short circuit current limit	I _F = 10 mA			80		μΑ
Cį	Junction capacitance	$V_{F} = 0,$	f = 1 MHz		12		pF

Coupler

PARAMETER			CONDITION	MIN	TYP†	MAX	UNIT	
1/4 [†]	Servo current gain			I _F = 1 mA	0.3%	0.7%	1.5%	
K1+				IF = 10 mA	0.5%	1.25%	2%	
K2§	Forward current gain			IF = 1 mA	0.3%	0.7%	1.5%	
K23	r orward current gam		Detector bias	$I_F = 10 \text{ mA}$	0.5%	1.25%	2%	
		TIL300	voltage = −15 V	$I_F = 1 \text{ mA}$	0.75	1	1.25	
кз¶	Transfer gain	TILSOO		I _F = 10 mA	0.75	1	1.25	
NO II	Transier gairi	TIL300A	1	IF = 1 mA	0.9	1	1.10	
		TIL300A		IF = 10 mA	0.9	1	1.10	
	Gain temperature coefficient	K1/K2	I _F = 10 mA			-0.5		%/°C
	Gain temperature coefficient	K3	TIF = TO THA			±0.005		70/°C
AV0#	Transfer gain linearity		I _F = 1 to 10 mA			±0.25%		
∆K3#	Transier gain inteanty		$I_F = 1$ to 10 mA,	$T_A = 0 \text{ to } 75^{\circ}\text{C}$		±0.5%		
BW	Bandwidth		$I_F = 10 \text{ mA},$ $I_F(\text{MODULATION}) = \pm 2 \text{ mA}$	$R_L = 1 k\Omega$,		200		kHz
t _r	Rise time		$I_F = 10 \text{ mA},$ $I_F(MODULATION) = \pm 2 \text{ mA}$	$R_L = 1 k\Omega$,		1.75		μs
t _f	Fall time		$I_F = 10 \text{ mA},$ $I_F(MODULATION) = \pm 2 \text{ mA}$	$R_L = 1 k\Omega$,		1.75		μs
∨ _{iso} †	Peak Isolation voltage		$I_{IO} = 10 \mu A$, time = 1 minute	f = 60 Hz	3535		·	٧

[†]This symbol is not currently listed within EIA or JEDEC standards for semiconductor symbology.



[‡] Servo current gain (K1) is the ratio of the feedback photodiode current (I_{P1}) to the input LED current (I_F) current (I_F), i.e. K1 = I_{P1}/I_F.

[§] Forward gain (K2 is the ratio of the output photodiode current (Ip2) to the input LED current (IF), i.e. K2 = Ip2/IF.

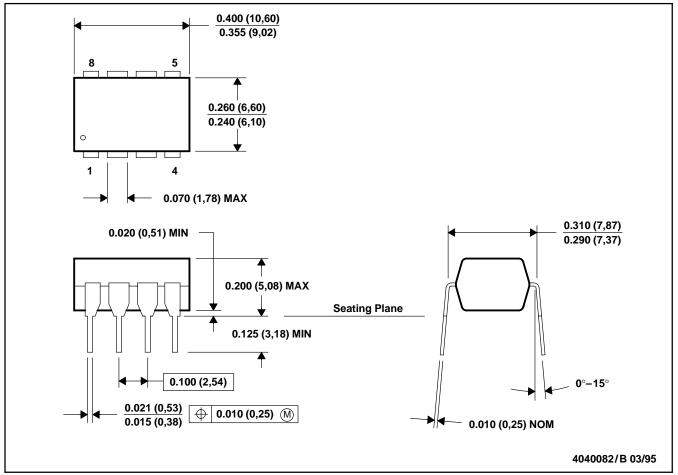
[¶] Transfer gain (K3) is the ratio of the forward gain to the servo gain, i.e. K3 = K2/K1.

[#] Transfer gain linearity (ΔK3) is the percent deviation of the transfer gain K3 as a function of LED input current (I_F) or the package temperature.

MECHANICAL DATA

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001

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